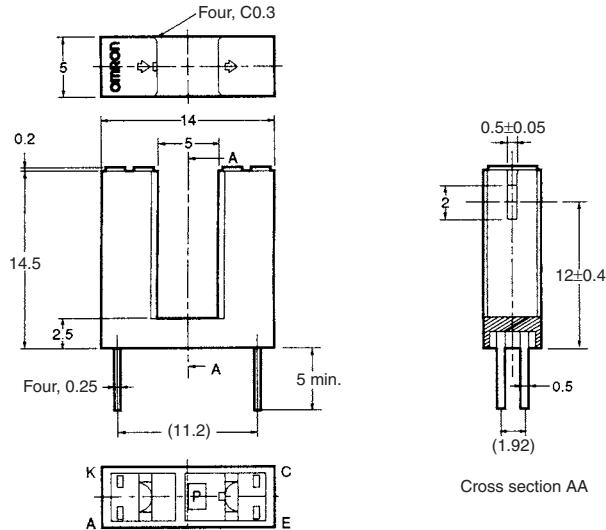


# Photomicrosensor (Transmissive) EE-SX1042

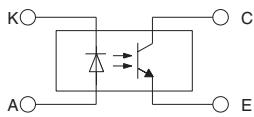
**⚠ Be sure to read *Precautions* on page 25.**

## ■ Dimensions

Note: All units are in millimeters unless otherwise indicated.



### Internal Circuit



Unless otherwise specified, the tolerances are as shown below.

Dimensions	Tolerance
3 mm max.	±0.3
3 < mm ≤ 6	±0.375
6 < mm ≤ 10	±0.45
10 < mm ≤ 18	±0.55
18 < mm ≤ 30	±0.65

## ■ Features

- 14.5-mm-tall model with a deep slot.
- PCB mounting type.
- High resolution with a 0.5-mm-wide aperture.

## ■ Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Rated value
Emitter	Forward current	I <sub>F</sub> 50 mA (see note 1)
	Pulse forward current	I <sub>FP</sub> 1 A (see note 2)
	Reverse voltage	V <sub>R</sub> 4 V
Detector	Collector-Emitter voltage	V <sub>CEO</sub> 30 V
	Emitter-Collector voltage	V <sub>ECO</sub> ---
	Collector current	I <sub>C</sub> 20 mA
	Collector dissipation	P <sub>C</sub> 100 mW (see note 1)
Ambient temperature	Operating	T <sub>opr</sub> -25°C to 85°C
	Storage	T <sub>stg</sub> -30°C to 100°C
Soldering temperature	T <sub>sol</sub>	260°C (see note 3)

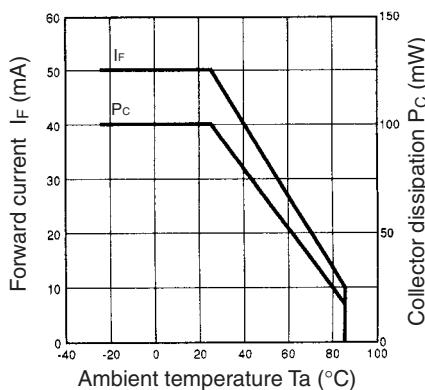
- Note:**
1. Refer to the temperature rating chart if the ambient temperature exceeds 25°C.
  2. The pulse width is 10 µs maximum with a frequency of 100 Hz.
  3. Complete soldering within 10 seconds.

## ■ Electrical and Optical Characteristics (Ta = 25°C)

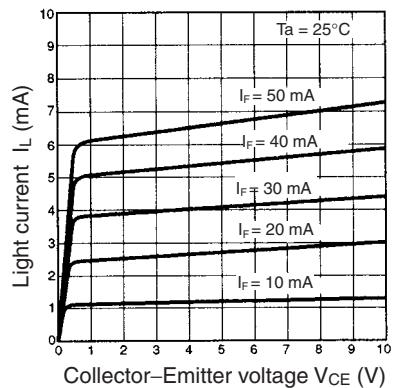
Item	Symbol	Value	Condition
Emitter	Forward voltage	V <sub>F</sub> 1.2 V typ., 1.5 V max.	I <sub>F</sub> = 30 mA
	Reverse current	I <sub>R</sub> 0.01 µA typ., 10 µA max.	V <sub>R</sub> = 4 V
	Peak emission wavelength	λ <sub>P</sub> 940 nm typ.	I <sub>F</sub> = 20 mA
Detector	Light current	I <sub>L</sub> 0.5 mA min., 10 mA max.	I <sub>F</sub> = 20 mA, V <sub>CE</sub> = 10 V
	Dark current	I <sub>D</sub> 2 nA typ., 200 nA max.	V <sub>CE</sub> = 10 V, 0 lux
	Leakage current	I <sub>LEAK</sub> ---	---
	Collector-Emitter saturated voltage	V <sub>CE</sub> (sat) 0.1 V typ., 0.4 V max.	I <sub>F</sub> = 20 mA, I <sub>L</sub> = 0.1 mA
	Peak spectral sensitivity wavelength	λ <sub>P</sub> 850 nm typ.	V <sub>CE</sub> = 10 V
Rising time	tr	4 µs typ.	V <sub>CC</sub> = 5 V, R <sub>L</sub> = 100 Ω, I <sub>L</sub> = 5 mA
Falling time	tf	4 µs typ.	V <sub>CC</sub> = 5 V, R <sub>L</sub> = 100 Ω, I <sub>L</sub> = 5 mA

## ■ Engineering Data

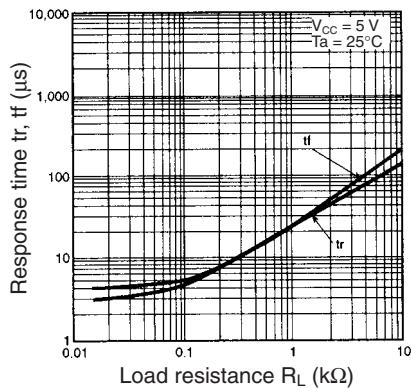
**Forward Current vs. Collector Dissipation Temperature Rating**



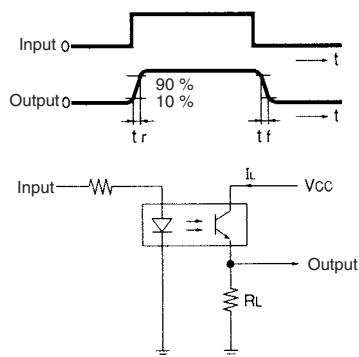
**Light Current vs. Collector-Emitter Voltage Characteristics (Typical)**



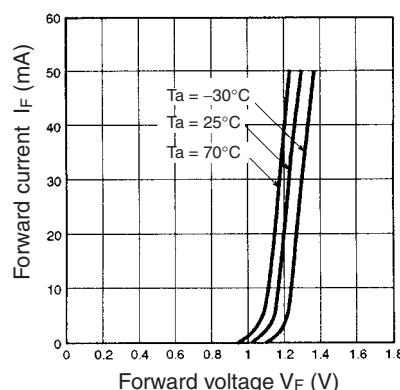
**Response Time vs. Load Resistance Characteristics (Typical)**



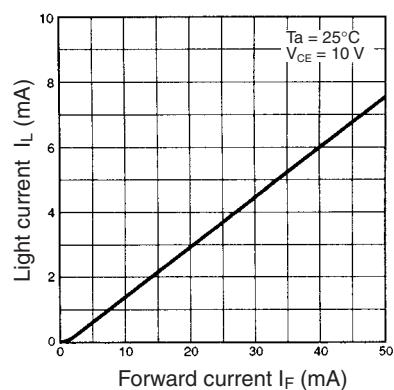
**Response Time Measurement Circuit**



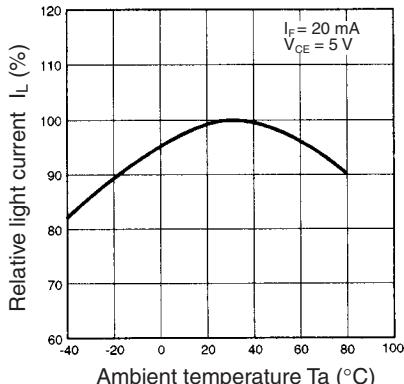
**Forward Current vs. Forward Voltage Characteristics (Typical)**



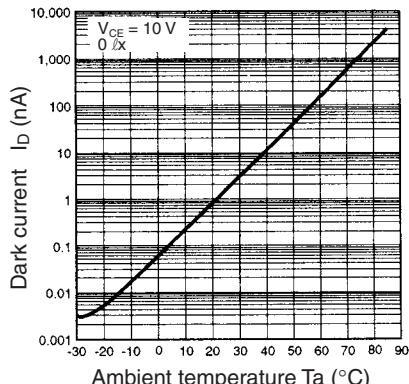
**Light Current vs. Forward Current Characteristics (Typical)**



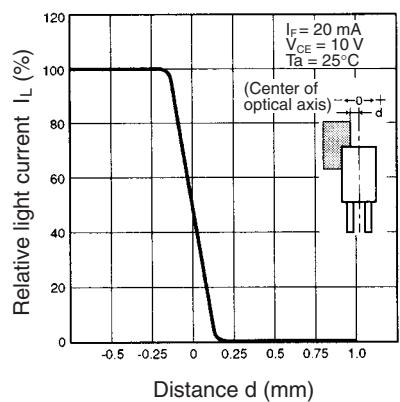
**Relative Light Current vs. Ambient Temperature Characteristics (Typical)**



**Dark Current vs. Ambient Temperature Characteristics (Typical)**



**Sensing Position Characteristics (Typical)**



**Sensing Position Characteristics (Typical)**

